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(54) Title: IN-SITU PHOTORESIST STRIP DURING PLASMA ETCHING OF ACTIVE HARD MASK

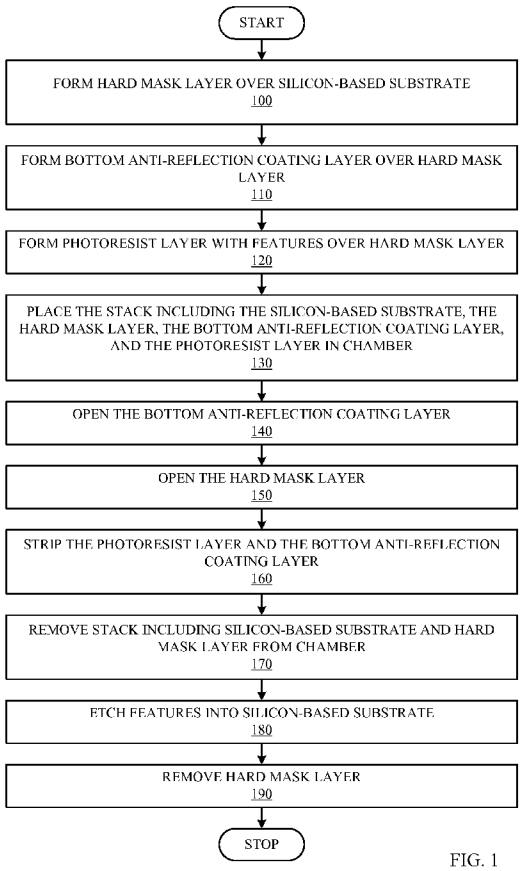


FIG. 1

(57) Abstract: A method for etching features in a silicon layer is provided. A hard mask layer is formed over the silicon layer. A photoresist layer is formed over the hard mask layer. The hard mask layer is opened. The photoresist layer is stripped by providing a stripping gas; forming a plasma with the stripping gas by providing a high frequency RF power and a low frequency RF power, wherein the low frequency RF power has a power less than 50 watts; and stopping the stripping gas when the photoresist layer is stripped. The opening the hard mask layer and the stripping the photoresist layer are performed in a same chamber.

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